

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 2000-138094

(43)Date of publication of application : 16.05.2000

(51)Int.Cl. H05B 33/10
C09K 11/00
C09K 11/56
C09K 11/88
C23C 16/30
G09F 13/20
H01L 21/205
H01L 21/365
H05B 33/14

(21)Application number : 11-229063

(71)Applicant : KOREA ELECTRONICS TELECOMMUN

(22)Date of filing : 13.08.1999

(72)Inventor : YUN SUN-JIN
KIN RYUSHIN
BOKU SOKI

(30)Priority

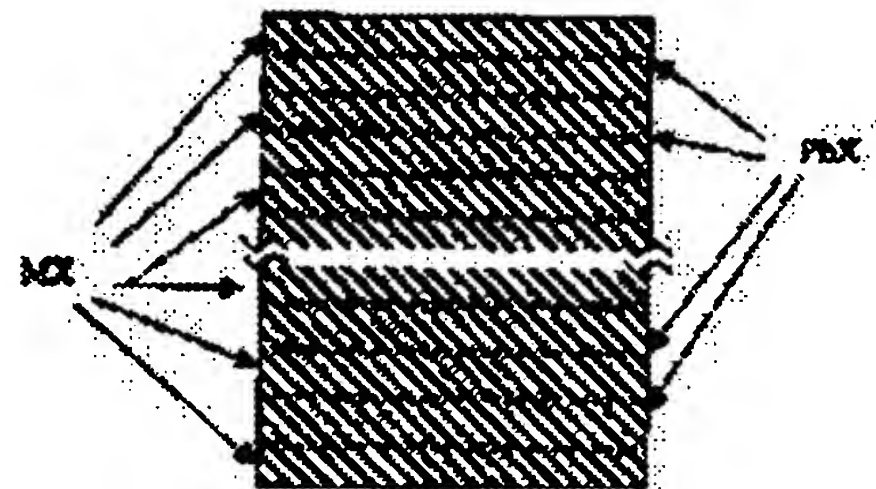
Priority number : 98 9833090 Priority date : 14.08.1998 Priority country : KR
99 9926897 05.07.1999 KR

(54) MANUFACTURE OF PBX (X/S OR Se) THIN FILM, AND ELECTRO- LUMINESCENT ELEMENT CONTAINING PBX AND ITS MANUFACTURE

(57)Abstract:

PROBLEM TO BE SOLVED: To uniformize thickness and to stabilize reactivity by growing a PbS thin film by the atomic layer vapor deposition method or the chemical vapor deposition method, using an organic metal compound.

SOLUTION: Regarding the method for manufacturing a PBX (X=S or Se) thin film, an organic metal compound containing Pb having a covalent binding with a working group is used as a Pb-precursor, and this precursor is reacted with H₂X (X=S or Se), thereby forming a PBX thin film. Also, regarding the method for manufacturing a luminescent material formed out of a base material for accelerating electrons and a light emitting zone containing luminescent center ions, a base material growth and a light emitting zone growth are separated from each other, and many are alternately made to grow repeatedly. In this case, the growth is caused by adjusting ions to be present as the status of Pb²⁺dimer as the light emitting center ions. In addition, a luminescent material having very high color purity and brightness is manufactured by adding the Pb²⁺ions in a selective and specific state, regardless of the wide concentration range of Pb²⁺.



LEGAL STATUS

[Date of request for examination]
[Date of sending the examiner's decision of rejection]
[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]
[Date of final disposal for application]
[Patent number]
[Date of registration]